



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-126C Plastic-Encapsulate Transistors

2SC3420 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 1.5 W ($T_{amb}=25^{\circ}C$)

Collector current

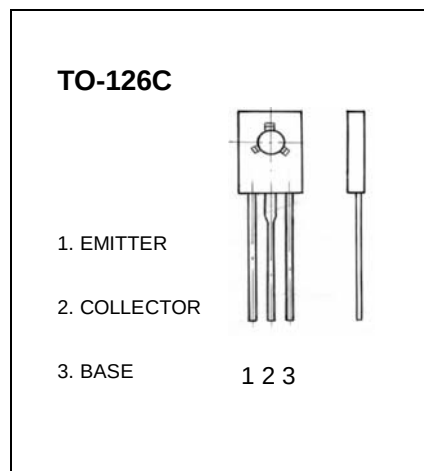
I_{CM} : 5 A

Collector-base voltage

$V_{(BR)CBO}$: 50 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	8			V
Collector cut-off current	I_{CBO}	$V_{CB}=40V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=8V, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2V, I_C=0.5A$	140		600	
	$h_{FE(2)}$	$V_{CE}=2V, I_C=4A$	70			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=4A, I_B=0.1A$			1	V
Base-emitter voltage	V_{BE}	$V_{CE}=2V, I_C=4A$			1.5	V
Transition frequency	f_T	$V_{CE}=2V, I_C=0.5A$		100		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		40		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	Y	GR	BL
Range	140-240	200-400	300-600
Marking			